High Reliability NPN Silicon Phototransistor

OP604TXV, OP604S

Obsolete (OP602(TX,TXV), OP603 (TX, TXV), OP604TX)

Electronics

Features:

- Miniature hermetically sealed package
- Wide range of collector currents
- Ideal for direct mounting to PCBoard
- TXV & S devices are processed to MIL-PRF-19500



Description:

Each device in the **OP600** high reliability series consists of a high-reliability NPN silicon phototransistor that is mounted in a glass-lensed miniature hermetically sealed "pill" package with an 18° half angle, as measured from the optical axis to the half-power point.

After electrical testing by manufacturing, devices are processed to OPTEK's 100 percent screening program, which is patterned after MIL-PRF-19500. Components in the high reliability OP600 series are mechanically and spectrally matched to the OP223 and OP224 high reliability series of infrared emitting diodes.

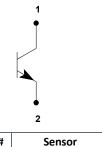
TXV and S devices are processed to OPTEK's military screening program patterned after MIL-PRF-19500.

<u>Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) and to Application Bulletin OP202 for pill-type soldering to PCBoard.</u>

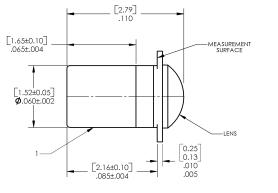
Applications:

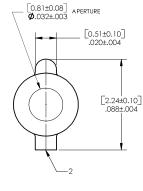
- Non-contact reflective object sensor
- · Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

Part Number	Light Current I _{C(ON)} (mA) Min / Max	V _{CE} Typ / Max	Input Power E _E (mW/cm²)	Viewing Angle
OP602TX Obsolete	2.00 / 5.00			35°
OP602TXV Obsolete	2.00 / 5.00			
OP603TX Obsolete	4.00 / 8.00			
OP603TXV Obsolete	4.00 / 8.00	5 / 50	20.0	
OP604S				
OP604TX Obsolete	7.00 / NA			
OP604TXV				



Pin #	Sensor		
1	Collector/Cathode		
2	Emitter/Anode		





DIMENSIONS ARE IN:

[MILLIMETERS]
INCHES

General Note

High Reliability NPN Silicon Phototransistor

OP604TXV, OP604S





Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature Range	-65° C to +150° C
Operating Temperature Range	-55° C to +125° C
Collector-Emitter Voltage	50 V
Emitter-Collector Voltage	7.0 V
Soldering Temperature (5 seconds with soldering iron) ⁽¹⁾	260° C
Power Dissipation ⁽²⁾	50 mW

Electrical Characteristics (T_A = 25° C unless otherwise noted)

Input Diode								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
I _{C(ON)}	On-State Collector Current OP604TXV, OP604S	7	-	-	mA	V _{CE} = 5.0 V, E _E = 20 mW/cm ²⁽³⁾⁽⁴⁾		
I _{CEO}	Callantan Bardi Connect		-	25	nA	V _{CE} = 10.0 V, E _E = 0		
	Collector Dark Current	-	-	100	μΑ	V _{CE} = 30.0 V, E _E = 0 T _A = 100° C		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	50	-	-	V	I _C = 100 μA, E _E = 0		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	7	-	-	V	I _C = 100 μA, E _E = 0		
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	0.4	V	$I_C = 0.4 \text{ mA}, E_E = 20 \text{ mW/cm}^{2(3)(4)}$		
t _f	Rise Time	-	-	20	μs	$V_{CC} = 30 \text{ V, } I_{C} = 1.00 \text{ mA,}$ $R_{L} = 100 \Omega^{(2)(3)(4)}$		
t _r	Fall Time	-	-	20				

Notes:

- (1) Refer to Application Bulleting 202, which discusses proper techniques for soldering pill-type devices to PCBoards.
- (2) No clean or low solids. RMA flux is recommended. Duration can be extended to 10 seconds maximum when wave soldering.
- (3) Derate linearly 0.5 mW/° C above 25° C.
- (4) Junction temperature maintained at 25° C.
- (5) Light source is an unfiltered tungsten lamp operating at CT=2870 K or equivalent source.

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